

MJE13003J1G (3DD13003J1G)

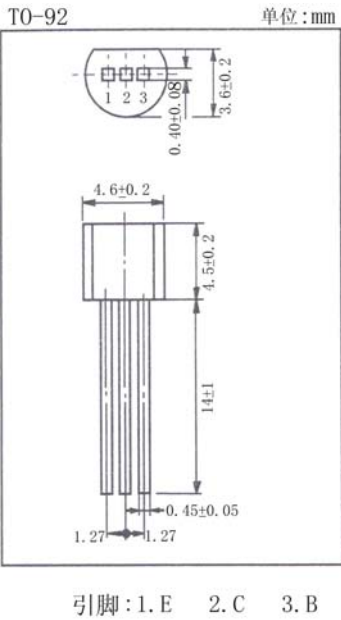
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	900	V
V _{CE0}	550	V
V _{EB0}	9.0	V
I _C	1.5	A
I _{CP}	3.0	A
P _C (Ta=25℃)	1.0	W
T _j	150	℃
T _{stg}	-55~150	℃

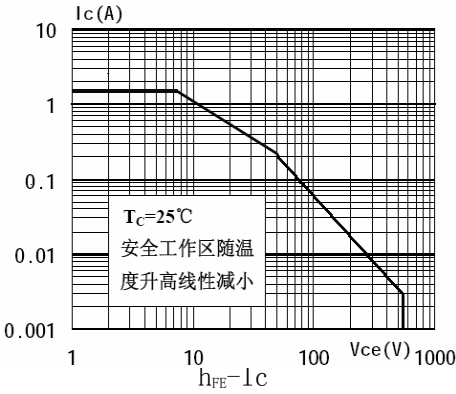


电性能参数/Electrical characteristics(Ta=25℃)

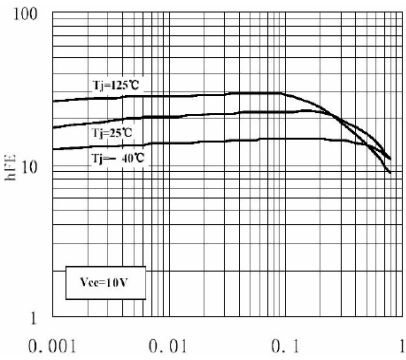
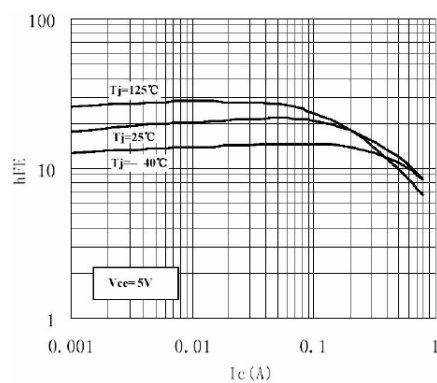
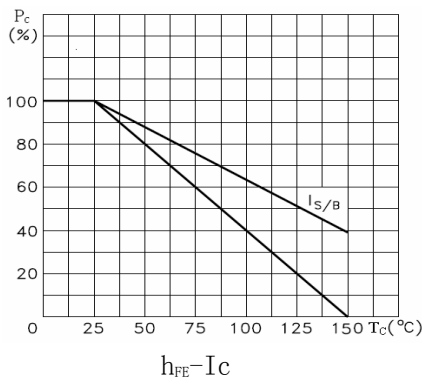
参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA I _E =0	900			V
V _{CE0}	I _C =10mA I _B =0	550			V
V _{EB0}	I _E =1mA I _C =0	9			V
I _{CB0}	V _{CB} =900V I _E =0			0.1	mA
I _{CE0}	V _{CE} =550V I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V I _C =0			0.1	mA
h _{FE(1)}	V _{CE} =10V I _C =400mA	10		40	
h _{FE(2)}	V _{CE} =10V I _C =1.0mA	13			
h _{FE(3)}	V _{CE} =10V I _C =1.0A	6			
V _{CE(sat) (1)}	I _C =1A I _B =0.25A			1	V
V _{CE(sat) (2)}	I _C =1.5A I _B =0.5A			2.5	V
V _{BE(sat)}	I _C =1A I _B =0.25A			1.5	V
f _T	V _{CE} =10V I _C =0.1A f=1.0MHz	5.0			MHz
t _f	V _{CE} =5V I _C =0.25A (UI9600)			1.2	μs
t _S		2		6	μs

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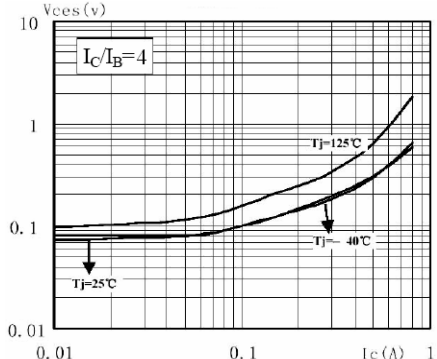
SOA (DC)



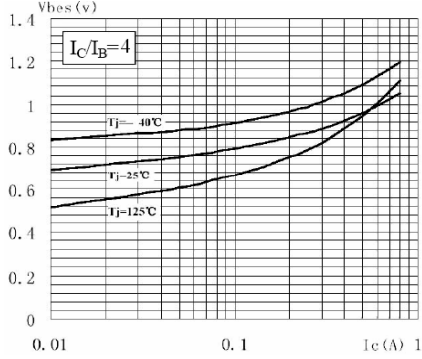
P_C-T_C



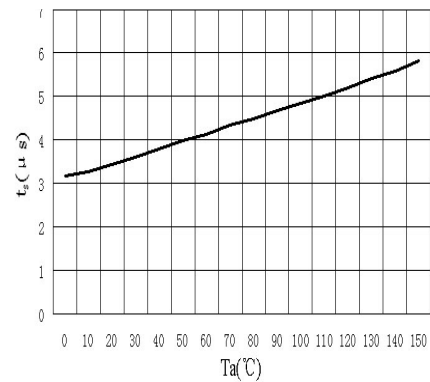
$V_{CES}-I_C$



$V_{BES}-I_C$



t_s-T_a



$h_{FE}-T_a$

